

SPEC SHEET (FOR REFERENCE)	SHEET No.	Rev.	Page.
	G05051A	2	1 of 1

TYPE:6PT2202P1T * *

CHIP SIZE	0.4 * 0.4mm
WAFER SIZE	6inch
POSSIBLE DIE PER WAFER	95,200pcs

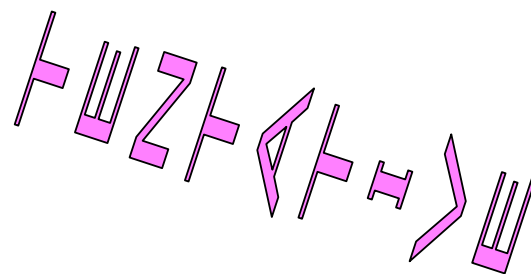
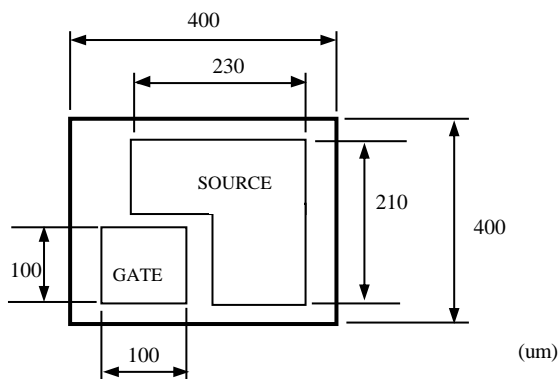
Maximum Ratings (Ta=25°C)

Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	-20	V
Gate-source voltage	VGSS	±8	V

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT			UNIT	CONDITIONS
		MIN.	Typ	MAX.		
1	IGSS1			±1	uA	VGS=±8V VDS=0V
2	IGSS2			±500	nA	VGS=±4.5V VDS=0V
3	IDSS			-1	uA	VDS=-20V VGS=0V
4	BVDSS	-22			V	ID=-10μA
5	VTH	-0.5		-1.2	V	ID=-250μA
6	RDS(on)1		0.6	1.1	Ω	VGS=-4.5V, ID=-430mA
7	RDS(on)2		1.0	1.6	Ω	VGS=-2.5V, ID=-300mA
8	RDS(on)3		1.5	2.4	Ω	VGS=-1.8V, ID=-10mA
9	VSD			1.1	V	I=-115mA VGS=0V
10	Yfs	200			mS	VDS=-10V Id=-200mA

※ Built-in ZD between Gate and Source.



NOTE: